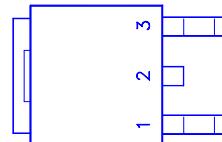
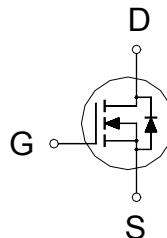


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
25	50mΩ	12A



1. GATE
2. DRAIN
3. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	12	A
		8	
Pulsed Drain Current ¹	I_{DM}	45	
Avalanche Energy	E_{AS}	60	mJ
Repetitive Avalanche Energy ²	E_{AR}	3	
Power Dissipation	P_D	48	W
		20	
Operating Junction & Storage Temperature Range	T_j, T_{stg}	-55 to 150	°C
Lead Temperature (1/16" from case for 10 sec.)	T_L	275	

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		3	
Junction-to-Ambient	$R_{\theta JA}$		75	°C / W
Case-to-Heatsink	$R_{\theta CS}$	1		

¹Pulse width limited by maximum junction temperature.

²Duty cycle ≤ 1%

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	Typ	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	25			V
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.8	1.2	2.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			25	μA
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125^\circ\text{C}$			250	
On-State Drain Current ¹	$I_{D(\text{ON})}$	$V_{DS} = 10V, V_{GS} = 10V$	12			A

NIKO-SEM
**N-Channel Logic Level Enhancement
Mode Field Effect Transistor**
P3057LD
TO-252 (DPAK)

Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 5V, I_D = 12A$		70	115	$m\Omega$
		$V_{GS} = 10V, I_D = 12A$		48	85	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 15V, I_D = 12A$		16		S

DYNAMIC

Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		450		pF
Output Capacitance	C_{oss}			200		
Reverse Transfer Capacitance	C_{rss}			60		
Total Gate Charge ²	Q_g	$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V,$ $I_D = 6A$		15		nC
Gate-Source Charge ²	Q_{gs}			2.0		
Gate-Drain Charge ²	Q_{gd}			7.0		
Turn-On Delay Time ²	$t_{d(on)}$			6.0		
Rise Time ²	t_r	$V_{DS} = 15V, R_L = 1\Omega$ $I_D \geq 12A, V_{GS} = 10V, R_{GS} = 2.5\Omega$		6.0		nS
Turn-Off Delay Time ²	$t_{d(off)}$			20		
Fall Time ²	t_f			5.0		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_C = 25^\circ C$)

Continuous Current	I_S	$I_F = I_S, V_{GS} = 0V$ $I_F = I_S, dI_F/dt = 100A/\mu s$		12		A
Pulsed Current ³	I_{SM}			20		
Forward Voltage ¹	V_{SD}			1.5		
Reverse Recovery Time	t_{rr}			30		
Peak Reverse Recovery Current	$I_{RM(REC)}$			15		
Reverse Recovery Charge	Q_{rr}			0.043		

¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.³Pulse width limited by maximum junction temperature.**REMARK: THE PRODUCT MARKED WITH "P3057LD", DATE CODE or LOT #**

NIKO-SEM

**N-Channel Logic Level Enhancement
Mode Field Effect Transistor**

**P3057LD
TO-252 (DPAK)**

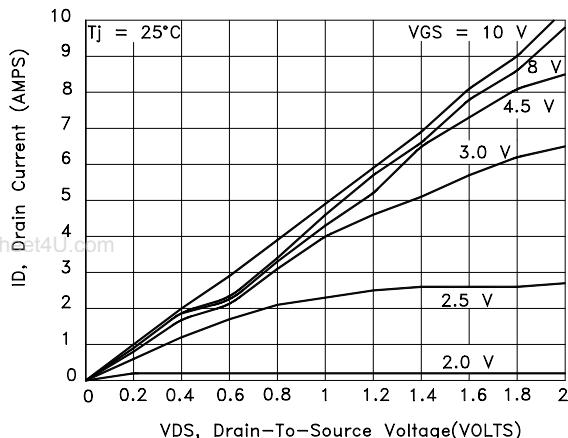


Fig.1 On-Resistance Variation with Temperature

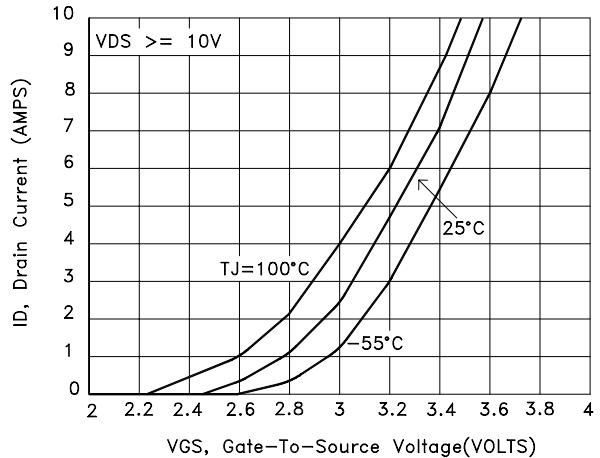


Fig.2 Transfer Characteristics

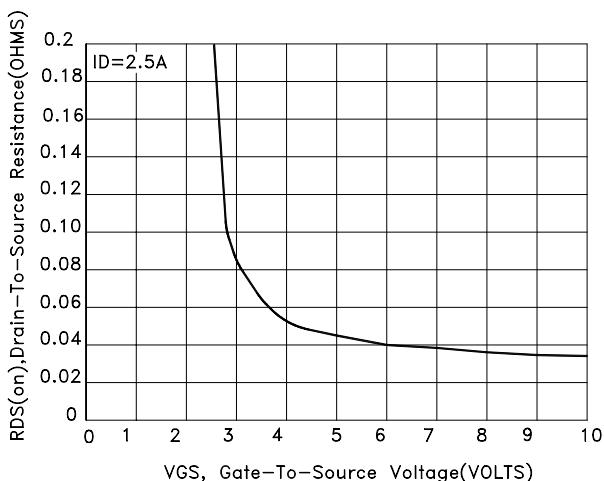


Fig.3 On-Resistance versus Gate-To-Source Voltage

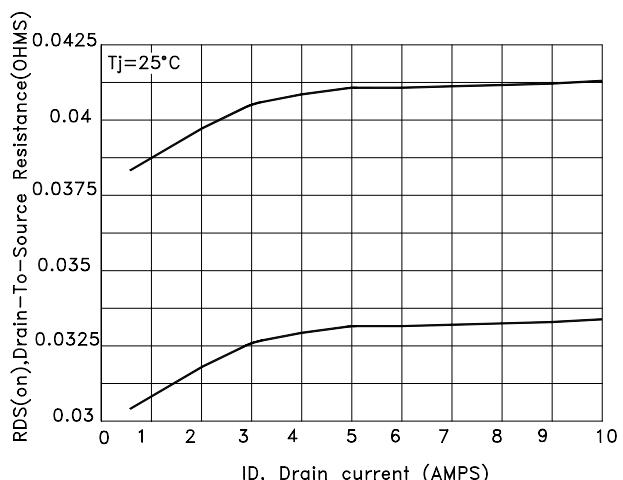


Fig.4 On-Resistance versus Drain Current and Gate Voltage

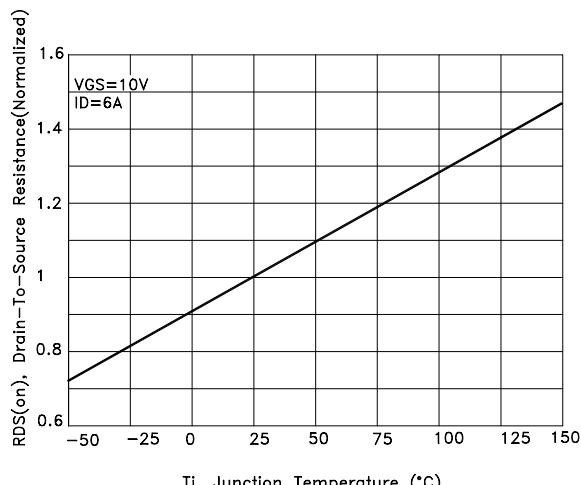


Fig.5 On-Resistance Variation with Temperature

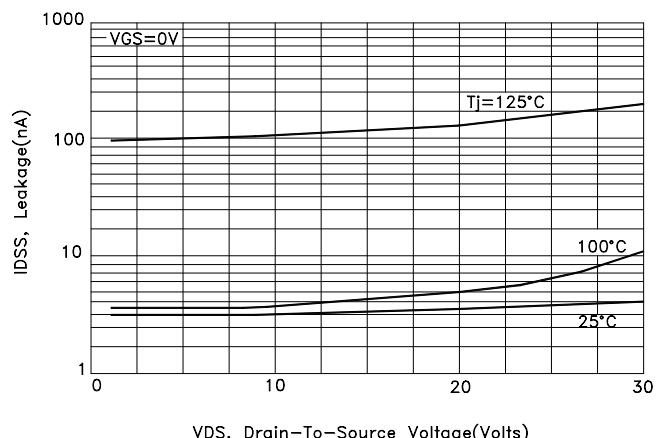


Fig.6 Drain-To-Source Leakage Current versus Voltage

TO-252 (DPAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	9.35		10.10	H		0.80	
B	2.20		2.40	I	6.40		6.60
C	0.48		0.85	J	5.00		5.50
D	0.89		1.50	K	0.55		1.10
E	0.45		0.60	L	0.60		1.00
F	0.03		0.23	M	4.40		4.60
G	5.20		6.20	N			

